



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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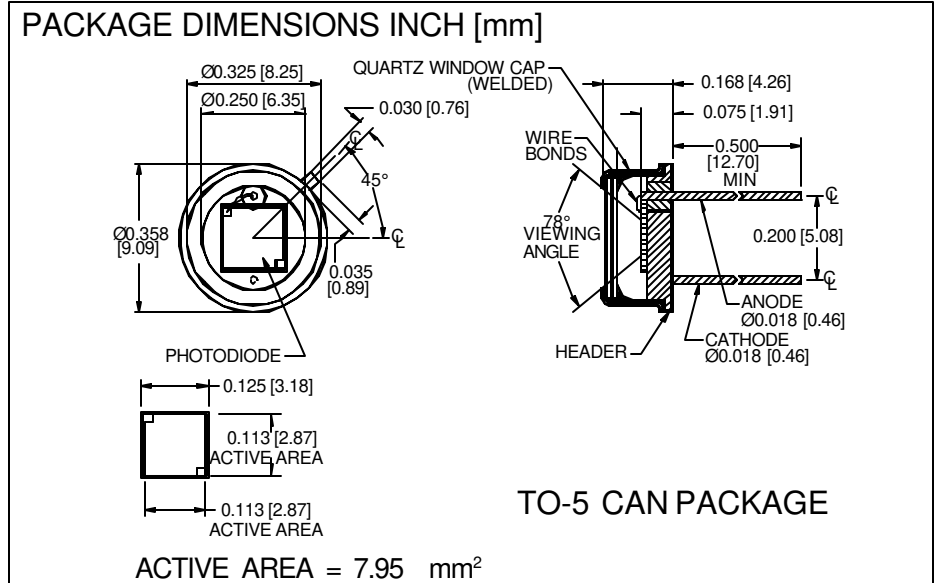
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PHOTONIC DETECTORS INC.

Silicon Photodiode, U.V. Enhanced Photoconductive Type PDU-C119-Q



FEATURES

- High speed
- U.V. enhanced
- Quartz window

DESCRIPTION

The **PDU-C119-Q** is a silicon, PIN planar diffused, U.V. enhanced photodiode. Ideal for high speed photoconductive U.V. applications. Packaged in a TO-5 metal can with a flat quartz window cap.

APPLICATIONS

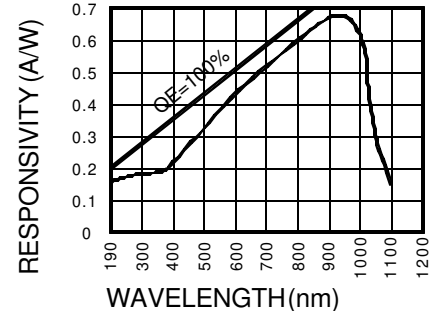
- Spectrometers
- Fluorescent analysers
- U.V. meters
- Colorimeters

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		30	V
T _{STG}	Storage Temperature	-55	+150	°C
To	Operating Temperature Range	-40	+125	°C
T _S	Soldering Temperature*		+240	°C
I _L	Light Current		500	mA

*1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{SC}	Short Circuit Current	E _c = 0.1 mW/cm ² , λ = 350 nm	.6	1.0		μA
I _D	Dark Current	H = 0, V _R = 5 V		2.5	5	nA
R _{SH}	Shunt Resistance	H = 0, V _R = 10 mV	150	300		MΩ
TC R _{SH}	RSH Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C
C _J	Junction Capacitance	H = 0, V _R = 5 V**		130		pF
λ _{range}	Spectral Application Range	Spot Scan	190		1100	nm
R	Responsivity	V _R = 0 V, λ = 254 nm	.12	.18		A/W
V _{BR}	Breakdown Voltage	I = 10 μA	15	25		V
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		2.2x10 ⁻¹⁴		W/√Hz
tr	Response Time	RL = 1 KΩ V _R = 5 V		58		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f = 1 MHz

[FORMNO. 100-PDU-C119-QREVA]